Preferred Device

# **Sensitive Gate Triacs**

# Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Sensitive Gate Triggering Uniquely Compatible for Direct Coupling to TTL, HTL, CMOS and Operational Amplifier Integrated Circuit Logic Functions
- Gate Triggering 4 Mode 2N6071A,B, 2N6073A,B, 2N6075A,B
- Blocking Voltages to 600 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Device Marking: Device Type, e.g., 2N6071A, Date Code

**MAXIMUM RATINGS** (T<sub>J</sub> =  $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage(1) (T <sub>J</sub> = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open) 2N6071A,B 2N6073A,B 2N6075A,B	V <sub>DRM,</sub> V <sub>RRM</sub>	200 400 600	Volts
*On-State RMS Current (T <sub>C</sub> = 85°C) Full Cycle Sine Wave 50 to 60 Hz	I <sub>T(RMS)</sub>	4.0	Amps
*Peak Non–repetitive Surge Current (One Full cycle, 60 Hz, TJ = +110°C)	ITSM	30	Amps
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	3.7	A <sup>2</sup> s
*Peak Gate Power (Pulse Width ≤ 1.0 μs, T <sub>C</sub> = 85°C)	PGM	10	Watts
*Average Gate Power (t = 8.3 ms, T <sub>C</sub> = 85°C)	PG(AV)	0.5	Watt
*Peak Gate Voltage (Pulse Width ≤ 1.0 μs, T <sub>C</sub> = 85°C)	V <sub>GM</sub>	5.0	Volts
*Operating Junction Temperature Range	Тj	-40 to +110	°C
*Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C
Mounting Torque (6-32 Screw) <sup>(2)</sup>	_	8.0	in. lb.

\*Indicates JEDEC Registered Data.

- (1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) Torque rating applies with use of a compression washer. Mounting torque in excess of 6 in. Ib. does not appreciably lower case-to-sink thermal resistance. Main terminal 2 and heatsink contact pad are common.



## **ON Semiconductor**

http://onsemi.com

# TRIACS 4 AMPERES RMS 200 thru 600 VOLTS





(formerly TO-126) CASE 077 STYLE 5

PIN ASSIGNMENT				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			

#### ORDERING INFORMATION

Device	Package	Shipping
2N6071A	TO225AA	500/Box
2N6071B	TO225AA	500/Box
2N6073A	TO225AA	500/Box
2N6073B	TO225AA	500/Box
2N6075A	TO225AA	500/Box
2N6075B	TO225AA	500/Box

Preferred devices are recommended choices for future use and best overall value.

Semiconductor Components Industries, LLC, 2000 May, 2000 – Rev. 3

#### THERMAL CHARACTERISTICS

Characteristic		Syn	nbol	Max	Unit		
*Thermal Resistance, Junction to Case		R <sub>0</sub>	JC	3.5	°(	C/W	
Thermal Resistance, Junction to Ambient		R <sub>e</sub>	JA	75	°(	°C/W	
Maximum Lead Temperature for Soldering Purposes 1/8" from	Case for 10 Secor	nds T	L	260 °		°C	
ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25°C unless o	therwise noted; Ele	ectricals apply i	n both direct	ions)	-		
Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			•	•		•	
*Peak Repetitive Blocking Current (V <sub>D</sub> = Rated V <sub>DRM</sub> , V <sub>RRM</sub> ; Gate Open)	T <sub>J</sub> = 25°C T <sub>J</sub> = 110°C	IDRM, IRRM			10 2	μA mA	
ON CHARACTERISTICS			•	•	•		
*Peak On-State Voltage <sup>(1)</sup> (I <sub>TM</sub> = ±6 A Peak)		V <sub>TM</sub>	-	-	2	Volts	
*Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = -4 All Quadrants	40°C)	VGT	_	1.4	2.5	Volts	
Gate Non–Trigger Voltage (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = 11 All Quadrants	10°C)	V <sub>GD</sub>	0.2	_	_	Volts	
*Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = $\pm 1$ Adc)	(T <sub>J</sub> = -40°C) (T <sub>J</sub> = 25°C)	ΙΗ	_	_	30 15	mA	
Turn-On Time (I <sub>TM</sub> = 14 Adc, I <sub>GT</sub> = 100 mAdc)	-	<sup>t</sup> gt	-	1.5	-	μs	
				QUAD (Maximu			
	Туре	<sup>I</sup> GT @ Т <sub>Ј</sub>	I mA	ll mA	III mA	IV mA	
Gate Trigger Current (Continuous dc)	2N6071A	+25°C	5	5	5	10	
(Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 ohms)	2N6073A 2N6075A	-40°C	20	20	20	30	
	2N6071B	+25°C	3	3	3	5	
	2N6073B 2N6075B	-40°C	15	15	15	20	
DYNAMIC CHARACTERISTICS				Į			

Critical Rate of Rise of Commutation Voltage	dv/dt(c)	—	5		V/µs
@ $V_{DRM}$ , $T_J = 85^{\circ}$ C, Gate Open, $I_{TM} = 5.7$ A, Exponential Waveform,					
Commutating di/dt = 2.0 A/ms				l !	

\*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

#### SAMPLE APPLICATION: TTL-SENSITIVE GATE 4 AMPERE TRIAC TRIGGERS IN MODES II AND III



Trigger devices are recommended for gating on Triacs. They provide:

- 1. Consistent predictable turn-on points.
- 2. Simplified circuitry.
- 3. Fast turn-on time for cooler, more efficient and reliable operation.

### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
VTM	Maximum On State Voltage
Ι <sub>Η</sub>	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

IC Logic	Firing Quadrant				
Functions	I	Ш	ш	IV	
TTL		2N6071A Series	2N6071A Series		
HTL		2N6071A Series	2N6071A Series		
CMOS (NAND)	2N6071B Series			2N6071B Series	
CMOS (Buffer)		2N6071B Series	2N6071B Series		
Operational Amplifier	2N6071A Series			2N6071A Series	
Zero Voltage Switch		2N6071A Series	2N6071A Series		

#### SENSITIVE GATE LOGIC REFERENCE





Figure 10. Thermal Response

### PACKAGE DIMENSIONS

**TO-225AA** (formerly TO-126) CASE 077-09 ISSUE W



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.425	0.435	10.80	11.04
В	0.295	0.305	7.50	7.74
С	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
Н	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
К	0.575	0.655	14.61	16.63
Μ	5°	TYP	5°	TYP
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040		1.02	

STYLE 5: PIN 1. MT 1 2. MT 2 3. GATE

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